



SHEET 1 OF 1

Form PTO 1449 (Modified)		U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE		ATTY DOCKET NO. 242452US2	PATENT & TRADEMARK OFFICE		SERIAL NO. 10/656,202
LIST OF REFERENCES CITED BY APPLICANT		APPLICANT		Yukio TANIGUCHI, et al.			
		FILING DATE		September 8, 2003			
U.S. PATENT DOCUMENTS							
EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
AA							
AB							
AC							
AD							
AE							
AF							
AG							
AH							
AI							
AJ							
AK							
AL							
AM							
AN							
FOREIGN PATENT DOCUMENTS							
		DOCUMENT NUMBER	DATE	COUNTRY	TRANSLATION		
AC	AO	6-289431	10/18/1994	JAPAN (with partial English translation)	YES	NO	X
AC	AP	2000-82669	03/21/2000	JAPAN (with English Abstract)	YES	NO	X
	AQ				YES	NO	
	AR				YES	NO	
	AS				YES	NO	
	AT				YES	NO	
OTHER REFERENCES (Including Author, Title, Date, Pertinent Pages, etc.)							
AC	AU	M. MATSUMURA, Applied Surface Science, vol. 21, no. 5, pages 278-287, "PREPARATION OF ULTRA-LARGE GRAIN SILICON THIN-FILMS BY EXCIMER-LASER", 2000 (with partial English translation)					
	AV	C.-H. OH, et al., Applied Surface Science 154-155, pages 105-111, "OPTIMIZATION OF PHASE-MODULATED EXCIMER-LASER ANNEALING METHOD FOR GROWING HIGHLY-PACKED LARGE-GRAINS IN Si THIN-FILMS", 2000					
	AW	M. MATSUMURA, Physica Status Solidi (a), vol. 166, no. 2, pages 715-728, "APPLICATION OF EXCIMER-LASER ANNEALING TO AMORPHOUS, POLY-CRYSTAL AND SINGLE-CRYSTAL SILICON THIN-FILM TRANSISTORS", 1998					
	AX	M. MATSUMURA, et al., Thin Solid Films, vol. 337, pages 123-128, "ADVANCED EXCIMER-LASER ANNEALING PROCESS FOR QUASI SINGLE-CRYSTAL SILICON THIN-FILM DEVICES", 1999					
	AY	C.-H. OH, et al., Japanese Journal of Applied Physics, vol. 37, no. 10, pages 5474-5479, "PREPARATION OF POSITION-CONTROLLED CRYSTAL-SILICON ISLAND ARRAYS BY MEANS OF EXCIMER-LASER ANNEALING", 1998					
AC	AZ	K. INOUE, et al., The Transactions of the Institute of Electronics, Information and Communication Engineers C, vol. J85-C, no. 8, pages 624-629, "AMPLITUDE AND PHASE MODULATED EXCIMER-LASER MELT-REGROWTH METHOD OF SILICON THIN-FILMS- A NEW GROWTH METHOD OF 2-D POSITION-CONTROLLED LARGE-GRAINS", 2002 (with partial English translation)			<input type="checkbox"/> Additional References sheet(s) attached		
Examiner <i>[Signature]</i>				Date Considered 8/29/05			

*Examiner: Initial if reference is considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.